

Features

- **Dual P-Channel MOSFET** •
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- **ESD Protected Up To 3KV**
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

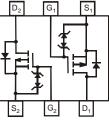
- Case: SOT-563 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)







BOTTOM VIEW



TOP VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

90 017 200 0100					
Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-20	V		
Gate-Source Voltage	V _{GSS}	±6	V		
Continuous Drain Current (Note 3) $V_{GS} = -4.5V$	I _D	-1.03 -0.68	А		
Pulsed Drain Current (Note 4)	I _{DM}	-3	А		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	530	mW
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 3)	R _{0JA}	235	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

1. No purposefully added lead. Notes:

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
Device mounted on FR-4 PCB, with minimum recommended pad layout.

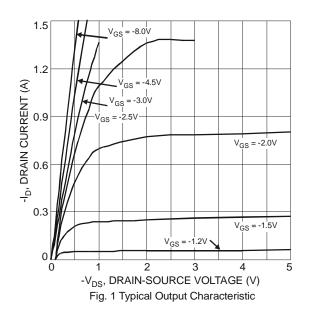
4. Repetitive rating, pulse width limited by junction temperature.

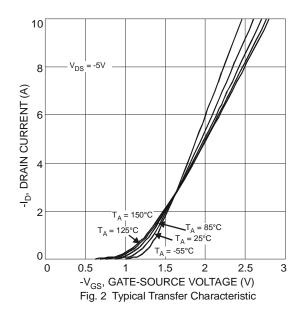


Electrical Characteristics @T_A = 25°C unless otherwise specified

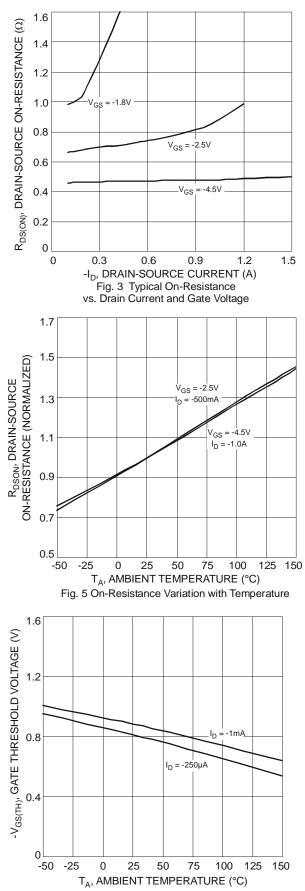
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)			-	-	-		
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±2.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	-0.5	-	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			0.5	0.75		$V_{GS} = -4.5V, I_D = -430mA$	
			0.7	1.05		$V_{GS} = -2.5V, I_D = -300mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	1.0	1.5	Ω	$V_{GS} = -1.8V, I_D = -150mA$	
			-	20		$V_{GS} = -1.7V, I_D = -100mA$	
			-	25		$V_{GS} = -1.5V, I_D = -100mA$	
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	V _{DS} = -10V, I _D = -250mA	
Diode Forward Voltage	V _{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	59.76	-	pF		
Output Capacitance	C _{oss}	-	12.07	-	pF	− V _{DS} = -16V, V _{GS} = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	6.36	-	pF	1 = 1.000	
Total Gate Charge	Qg	-	622.4	-	рС		
Gate-Source Charge	Q _{gs}	-	100.3	-	рС	$V_{GS} = -4.5V, V_{DS} = -10V,$	
Gate-Drain Charge	Q _{gd}	-	132.2	-	рС	$-I_D = -250 \text{mA}$	
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns		
Turn-On Rise Time	tr	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	$R_{L} = 47\Omega, R_{G} = 10\Omega,$ $I_{D} = -200 \text{mA}$	
Turn-Off Fall Time	t _f	-	20.7	-	ns	-ID = -200IIIA	

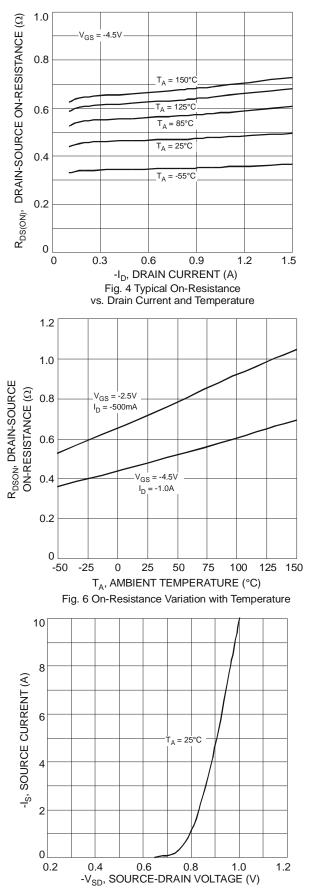
Notes: 5. Short duration pulse test used to minimize self-heating effect. 6. Guaranteed by design. Not subject to production testing.





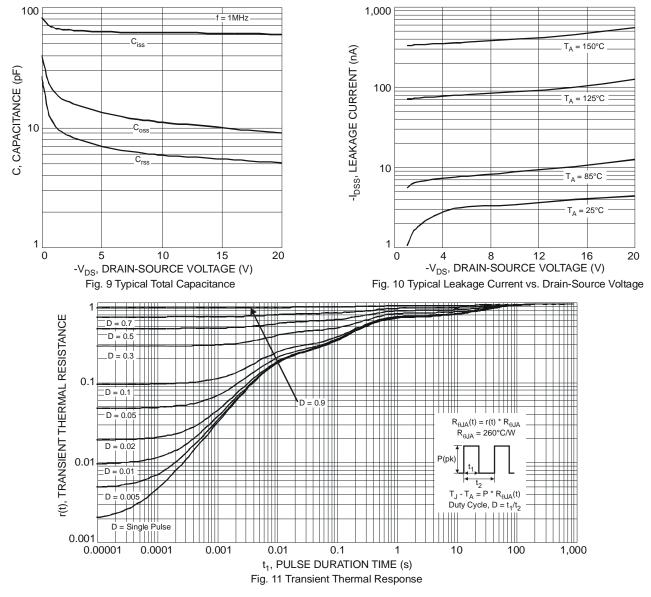








DMG1023UV

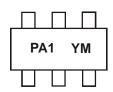


Ordering Information (Note 7)

Part Number	Case	Packaging
DMG1023UV-7	SOT-563	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

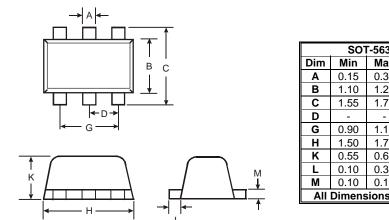


PA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key												
Year	2008	2	009	2010	2	2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

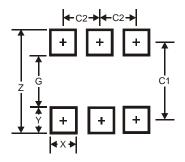


Package Outline Dimensions



SOT-563					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.20		
В	1.10	1.25	1.20		
С	1.55	1.70	1.60		
D	-	-	0.50		
G	0.90	1.10	1.00		
Н	H 1.50 1.70 1.60				
Κ	0.55	0.60	0.60		
L	0.10	0.30	0.20		
М	0.10	0.18	0.11		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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